



Final Product/Process Change Notification

Document # : FPCN22134XJ

Issue 13 February 2019

Title of Change:	Hydrazine elimination in ON Semiconductor Niigata Co., Ltd., Japan (OSNC).	
Proposed first ship date:	20 May 2019	
Contact information:	Contact your local ON Semiconductor Sales Office or <Yukio.Kudo@onsemi.com>	
Samples:	Contact your local ON Semiconductor Sales Office or <PCN.samples@onsemi.com> Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change.	
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or <Satoru.Fujinuma@onsemi.com>	
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <PCN.Support@onsemi.com>	
Change Part Identification:	Date Code	
Change Category:	<input checked="" type="checkbox"/> Wafer Fab Change <input type="checkbox"/> Assembly Change <input type="checkbox"/> Test Change <input type="checkbox"/> Other _____	
Change Sub-Category(s):	<input type="checkbox"/> Manufacturing Site Addition <input type="checkbox"/> Material Change <input type="checkbox"/> Datasheet/Product Doc change <input type="checkbox"/> Manufacturing Site Transfer <input type="checkbox"/> Product specific change <input type="checkbox"/> Shipping/Packaging/Marking <input checked="" type="checkbox"/> Manufacturing Process Change <input type="checkbox"/> Other: _____	
Sites Affected:	ON Semiconductor Sites: ON Niigata, Japan	External Foundry/Subcon Sites: None
Description and Purpose:		
<p>This Final notification announces the elimination of Hydrazine in ON Semiconductor Niigata Co., Ltd. Japan for parts listed in this PCN. Hydrazine was identified as a prohibited chemical in ON Semiconductor as it is considered as a carcinogenic substance and has high risk of fire and explosion. The related products are transferred to a process that does not use Hydrazine on the same site ON Semiconductor Niigata, Japan (OSNC).</p>		
Change Point	Before Change Description	After Change Description
Fab (OSNC)	N1 Fab (Minimum rule=0.8um, Class=10)	N1 Fab (Minimum rule=0.8um, Class=10) AND N2 Fab (Minimum rule=0.25um, Class=1)
Wire material	Aluminum (without Anti-reflected Layer)	Aluminium (with Anti-reflected Layer)
Interlayer material	Silicon nitride and Polyimide or Polyimide	Silicon nitride and Silicon oxide or Oxide

**Reliability Data Summary:**

QV DEVICE NAME : LB11870-TRM-E

PACKAGE:HSSOP48(375mil)

Test	Specification	Condition	Interval	Results
HTOL	JESD22-A108	Tj=150°C, 100 % max rated Vcc	1008 hrs	0/77
HTSL	JESD22-A103	Ta= 150°C	1008 hrs	0/77
TC	JESD22-A104	Ta= -65°C to +150°C	500 cyc	0/77
THB	JESD22-A101	85°C, 85% RH, bias	1008 hrs	0/77
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig,	96 hrs	0/77
PC	J-STD-020 JESD-A113	MSL 3 @ 260 °C	-	PASS
HBM	JS001	100pF,1.5kohm,+/-1kV	-	0/3
CDM	JS002	+/-500V	-	0/3

Electrical Characteristic Summary:

There is no change in the electrical performance. Datasheet specifications remain unchanged.

List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the **PCN Customized Portal**.

Part Number	Qualification Vehicle
LA6588MC-W-AH	LB11870-TRM-E
LB11660FV-W-AH	LB11870-TRM-E
LB11660RV-W-AH	LB11870-TRM-E
LB11685AV-W-AH	LB11870-TRM-E
LB11850VA-W-AH	LB11870-TRM-E
LB11868V-W-AH	LB11870-TRM-E
LB11961-W-AH	LB11870-TRM-E
LB11967V-W-AH	LB11870-TRM-E
LB11970FV-W-AH	LB11870-TRM-E
LB1948MC-AH	LB11870-TRM-E
LB1973JA-AH	LB11870-TRM-E
LB1936V-TLM-E	LB11870-TRM-E
LB1939T-TLM-E	LB11870-TRM-E
LB1940T-TLM-H	LB11870-TRM-E

Japanese translation of the notification starts here.
通知の日本語訳はここから始まります。

Note: The Japanese version is for reference only. In case of any differences between the English and Japanese version, the English version shall control.

注：日本語版は参照用です。英語版と日本語版の違いがある場合は、英語版が優先されます。



信頼性データの要約:

QV 素子名: LB11870-TRM-E

パッケージ: HSSOP48 (375 mil)

テスト	仕様	条件	間隔	結果
HTOL	JESD22-A108	Tj=150°C, 100 % max rated Vcc	1008 hrs	0/77
HTSL	JESD22-A103	Ta= 150°C	1008 hrs	0/77
TC	JESD22-A104	Ta= -65°C to +150°C	500 cyc	0/77
THB	JESD22-A101	85°C, 85% RH, bias	1008 hrs	0/77
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig,	96 hrs	0/77
PC	J-STD-020 JESD-A113	MSL 3 @ 260 °C	-	PASS
HBM	JS001	100pF,1.5kohm,+/-1kV	-	0/3
CDM	JS002	+/-500V	-	0/3

電気的特性の要約:

電気的性能に変更はありません。データシートの仕様に変更はありません。

影響を受ける部品の一覧:

注: 部品一覧には標準部品番号 (既製品) のみが記載されています。本 PCN の影響を受けるカスタム部品番号は、PCN メールで提供される顧客個別の付録、または PCN カスタマイズポータルに記載されています。

部品番号	品質試験用ピークル
LA6588MC-W-AH	LB11870-TRM-E
LB11660FV-W-AH	LB11870-TRM-E
LB11660RV-W-AH	LB11870-TRM-E
LB11685AV-W-AH	LB11870-TRM-E
LB11850VA-W-AH	LB11870-TRM-E
LB11868V-W-AH	LB11870-TRM-E
LB11961-W-AH	LB11870-TRM-E
LB11967V-W-AH	LB11870-TRM-E
LB11970FV-W-AH	LB11870-TRM-E
LB1948MC-AH	LB11870-TRM-E
LB1973JA-AH	LB11870-TRM-E
LB1936V-TLM-E	LB11870-TRM-E
LB1939T-TLM-E	LB11870-TRM-E
LB1940T-TLM-H	LB11870-TRM-E

Appendix A: Changed Products

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Product	Customer Part Number	Qualification Vehicle
LA6588MC-W-AH		LB11870-TRM-E
LB11660FV-W-AH		LB11870-TRM-E
LB11660RV-W-AH		LB11870-TRM-E
LB11685AV-W-AH		LB11870-TRM-E
LB11850VA-W-AH		LB11870-TRM-E
LB11868V-W-AH		LB11870-TRM-E
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LB11967V-W-AH		LB11870-TRM-E
LB11970FV-W-AH		LB11870-TRM-E
LB1936V-TLM-E		LB11870-TRM-E
LB1939T-TLM-E		LB11870-TRM-E
LB1940T-TLM-H		LB11870-TRM-E
LB1948MC-AH		LB11870-TRM-E
LB1973JA-AH		LB11870-TRM-E